Specifications

Parameter	Value
OFET	
Substrate (Gate)	n-doped silicon (doping at wafer surface: n~3·10^{17} cm^{-3}), 150 mm wafer according to SEMI standard (675 ± 20 µm thickness)
Gate Oxide	230 ± 10 nm SiO_2 (thermal oxidation) Other oxide thicknesses (90 … 500 nm) can be realized upon request
Contacts (Drain/Source)	30 nm Au with 10 nm high work function adhesion layer (ITO) (structured by lift-off technique)
Test Chip Size	15 × 15 mm²
Test Chip Transistor Configurations	**Gen. 4** / **Gen. 5** / **Customer Layout** 4 transistors L = 2.5 µm — W = 10 mm / W = 2 mm / available upon request 4 transistors L = 5 µm — W = 10 mm / W = 2 mm 4 transistors L = 10 µm — W = 10 mm / W = 2 mm 4 transistors L = 20 µm — W = 10 mm / W = 2 mm Contact pads 0.5 × 0.5 mm²
Shipment Type	Diced wafer (60 test chips at 15 × 15 mm²) on foil with air tight packaging Resist protection layer AZ7217 (soluble in AZ thinner or acetone)
OFET (trimmed)	
Substrate (Gate)	n-doped silicon (doping at wafer surface: n~3·10^{17} cm^{-3}), 150 mm wafer according to SEMI standard (675 ± 20 µm thickness)
Gate Oxide	230 ± 10 nm SiO_2 (thermal oxidation) Other thicknesses from 10 nm to 500 nm are available upon request
Test Chip Size	15 × 15 mm² (standard), other sizes are available upon request
Shipment Type	Diced wafer (60 test chips at 15 × 15 mm²) on foil with air tight packaging Resist protection layer AZ7217 (soluble in AZ thinner or acetone) Undiced wafer also available upon request
LOFET	
Wafer	150 mm according to SEMI standard
Structure Classes	11 transistors, 4 inverters and 4 ring oscillators; additional technology test structures
Die Size	15 × 15 mm²
Number of Dies	60
Number of Pads	39 + 2
Pad Size	1200 × 800 µm²
Gate Oxide	200 ± 10 nm
Structured Layers	3 (gate, contacts, drain/source)
Source/Drain Layer	Ti/TiN, Rs approx. 10 Ω/sq.
Contacts	Standard 20 × 20 µm², R approx. 20 Ω
Top Layer	70 nm Au with 10 nm high work adhesion layer (ITO, structured by lift-off technique) Rs approx. 0.65 Ω/sq. / 0.45 Ω/sq.
Shadow Mask	possible, but not required
Probecard	possible, but not required
Shipment Type	Diced wafer (60 test chips) on foil with air tight packaging Resist protection layer AZ7217 (soluble in AZ thinner or acetone)
OFET Miniprober	
Size	120 mm × 110 mm × 35 mm
Wight	280 g
Material	Body: Aluminium, PCB: FR4
Contacts	Top side: spring contacts, gold plated, 0.33 mm diameter; Back side: FR4, gold plated
Connector	3 × BNC, Triaxial upon request
Functionality	Up-down movement of a thread and adjusting knob Warning! Do not use with hazardous voltages (>100V)